Nathaniel E Richey

List of Publications by Year
in descending order

12	283	1307594 7	1199594 12
papers	citations	h-index	g-index

12	12	12	452
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Methyl-methacrylate based aluminum hybrid film grown via three-precursor molecular layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 023405.	2.1	2
2	Molecular Layer Deposition of a Hafnium-Based Hybrid Thin Film as an Electron Beam Resist. ACS Applied Materials & Interfaces, 2022, 14, 27140-27148.	8.0	11
3	Understanding and Utilizing Reactive Oxygen Reservoirs in Atomic Layer Deposition of Metal Oxides with Ozone. Chemistry of Materials, 2022, 34, 5584-5597.	6.7	4
4	Elucidating the Reaction Mechanism of Atomic Layer Deposition of Al₂O₃ with a Series of Al(CH₃)_xCl_{3â€“x} and Al(C_yH_{2y+1})₃ Precursors. Journal of the American Chemical Society, 2022, 144, 11757-11766.	13.7	8
5	Multi-metal coordination polymers grown through hybrid molecular layer deposition. Dalton Transactions, 2021, 50, 4577-4582.	3.3	5
6	Role of Precursor Choice on Area-Selective Atomic Layer Deposition. Chemistry of Materials, 2021, 33, 3926-3935.	6.7	30
7	Mechanistic Study of Nucleation Enhancement in Atomic Layer Deposition by Pretreatment with Small Organometallic Molecules. Chemistry of Materials, 2020, 32, 315-325.	6.7	32
8	Modified atomic layer deposition of MoS2 thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	14
9	Understanding chemical and physical mechanisms in atomic layer deposition. Journal of Chemical Physics, 2020, 152, 040902.	3.0	143
10	N,N-Disubstituted-Nâ€²-acylthioureas as modular ligands for deposition of transition metal sulfides. Dalton Transactions, 2018, 47, 2719-2726.	3.3	16
11	Synthesis and Characterization of Tungsten Nitrido Amido Guanidinato Complexes as Precursors for Chemical Vapor Deposition of WN x C y Thin Films. European Journal of Inorganic Chemistry, 2018, 2018, 46-53.	2.0	5
12	Aerosol-assisted chemical vapor deposition of WS₂ from the single source precursor WS(S₂)(S₂CNEt₂)₂. Chemical Communications, 2017, 53, 7728-7731.	4.1	13